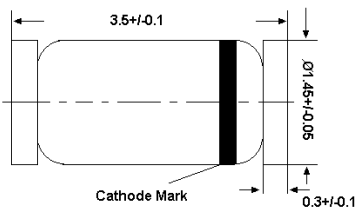


Silicon Epitaxial Planar Switching Diode

Feature

- Fast switching diode in MiniMELF case especially suited for automatic surface mounting

LL-34



Glass case MiniMELF
Dimensions in mm

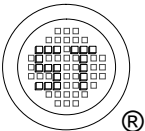
Absolute Maximum Ratings (T_a = 25°C)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V _{RM}	100	V
Reverse Voltage	V _R	75	V
Average Rectified Forward Current	I _{F(AV)}	200	mA
Non-repetitive Peak Forward Surge Current	I _{FSM}	0.5	A
at t = 1 s		1	
at t = 1 ms		4	
at t = 1 μs			
Power Dissipation	P _{tot}	500	mW
Junction Temperature	T _j	175	°C
Storage Temperature Range	T _{stg}	- 65 to + 175	°C

Thermal Characteristics

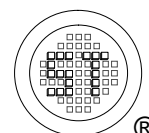
Parameter	Symbol	Max.	Unit
Thermal Resistance from Junction Ambient ¹⁾	R _{θJA}	300	°C/W

¹⁾Valid provided that electrodes are kept at ambient temperature.



Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage tested with 100 μA Pulses	$V_{(BR)R}$	100	-	V
Forward Voltage at $I_F = 10\text{ mA}$	V_F	-	1	V
Leakage Current at $V_R = 20\text{ V}$ at $V_R = 75\text{ V}$ at $V_R = 20\text{ V}$, $T_j = 150^\circ\text{C}$	I_R I_R I_R	- - -	25 5 50	nA μA μA
Capacitance at $V_R = 0\text{ V}$, $f = 1\text{ MHz}$	C_{tot}	-	4	pF
Voltage Rise when Switching on tested with 50 mA Forward Pulses $t_p = 0.1\text{ s}$, Rise Time < 30 ns, $f_p = 5\text{ to }100\text{ KHz}$	V_{fr}	-	2.5	V
Reverse Recovery Time at $I_F = 10\text{ mA}$, $I_{rr} = 0.1 \times I_R$, $V_R = 6\text{ V}$, $R_L = 100\ \Omega$	t_{rr}	-	4	ns



Electrical Characteristics Curves

Fig 1. Forward Characteristics

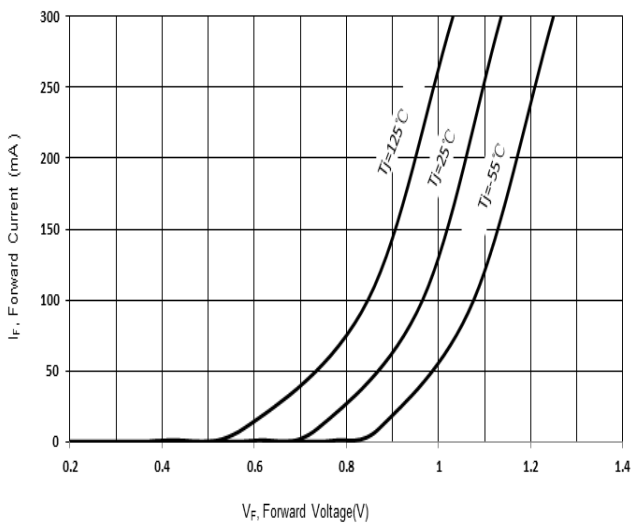


Fig 2. Reverse Characteristics

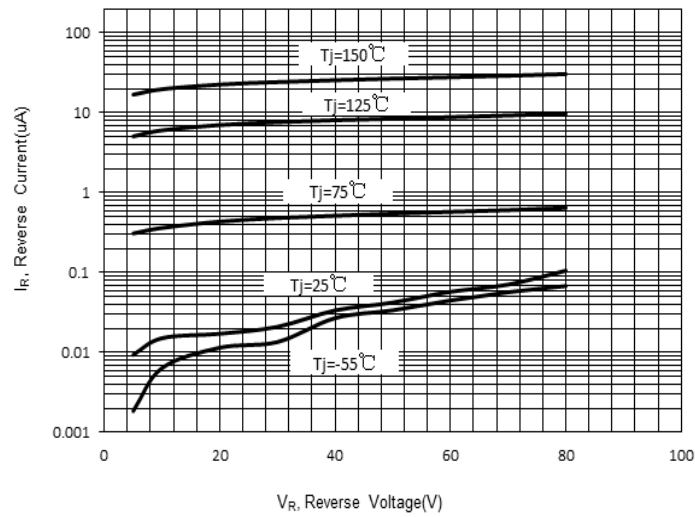


Fig 3. Junction Capacitance

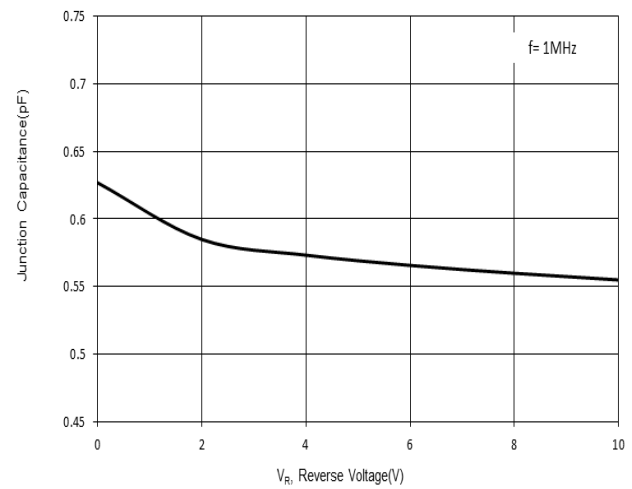


Fig 4. Power Derating Curves

